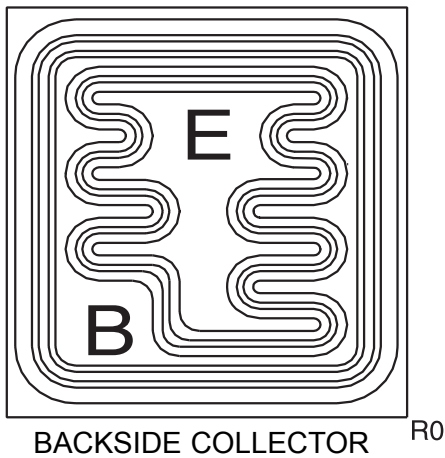


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	19 x 19 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



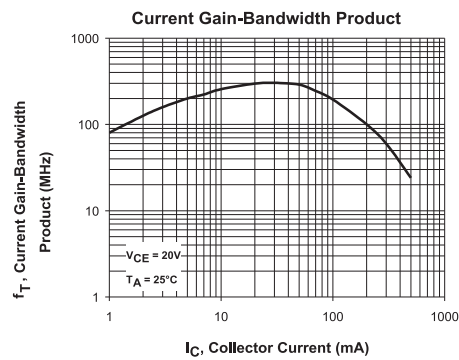
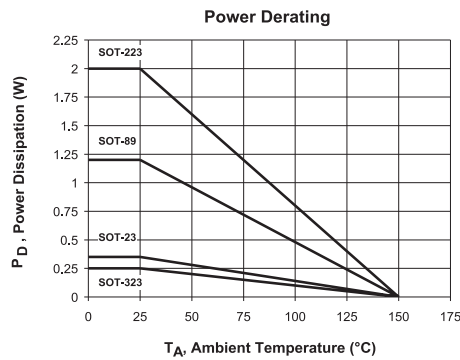
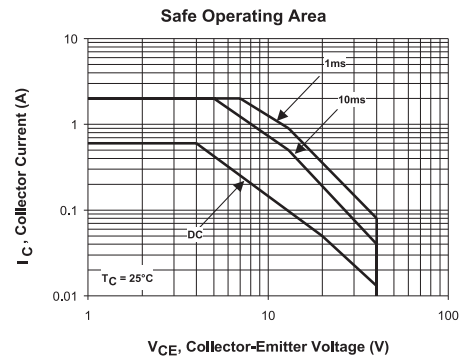
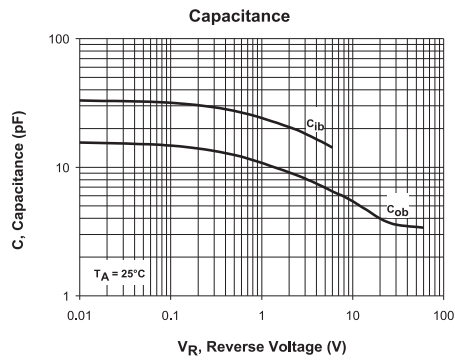
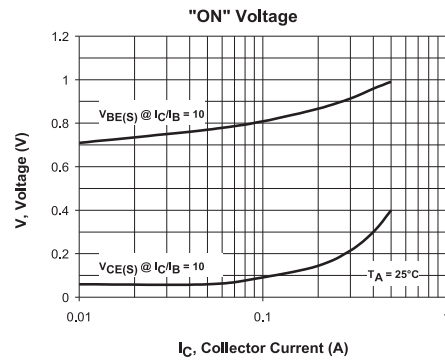
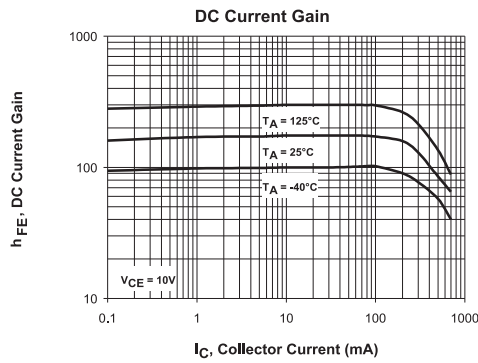
GROSS DIE PER 4 INCH WAFER
30,600

PRINCIPAL DEVICE TYPES

2N2905A
2N2907A
CMPT2907A
CMST2907A
CXT2907A
CZT2907A
PN2907A

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R3 (1-August 2002)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R3 (1-August 2002)